

March 1999

### **FDC6305N**

### Dual N-Channel 2.5V Specified PowerTrench™ MOSFET

### **General Description**

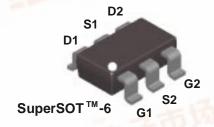
These N-Channel low threshold 2.5V specified MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

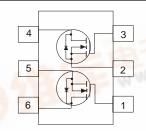
### **Applications**

- Load switch
- DC/DC converter
- Motor driving

### **Features**

- 2.7 A, 20 V.  $R_{DS(ON)} = 0.08 \Omega$  @  $V_{GS} = 4.5 V$  $R_{DS(ON)} = 0.12 \Omega @ V_{GS} = 2.5 V$
- Low gate charge (3.5nC typical).
- Fast switching speed.
- High performance trench technology for extremely low R<sub>DS(ON)</sub>.
- SuperSOT<sup>TM</sup>-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).





Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units	
V <sub>DSS</sub>	Drain-Source Voltage		20	V	
V <sub>GSS</sub>	Gate-Source Voltage		±8	V	
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	2.7	A	
	- Pulsed	1 th	8	1.0	
P <sub>D</sub>	Power Dissipation for Single Operation	(Note 1a)	0.96	W	
	or EAR	(Note 1b)	0.9		
	一二方向四	(Note 1c)	0.7		
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature	Range	-55 to +150	°C	
Therma	I Characteristics				
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	130	°C/W	
R <sub>OJC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	60	°C/W	

Package Outlines and Ordering Information

	1 dokage oddinies and ordering information										
	Device Marking	Device	Reel Size	Tape Width	Quantity						
DE	.305	FDC6305N	7"	8mm	3000 units						

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Off Char	acteristics						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250  \mu\text{A}$	20			V	
<u>∆</u> BVdss ∆TJ	Breakdown Voltage Temperature Coefficient	g ,					
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0 V			1	μΑ	
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 8 V, V <sub>DS</sub> = 0 V			100	nA	
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	$V_{GS} = -8 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA	
On Char	acteristics (Note 2)						
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250  \mu A$	0.4	0.9	1.5	V	
$\Delta VGS(th) \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		-2.7		mV/∘C	
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 4.5$ , $I_D = 2.7$ A $V_{GS} = 4.5$ $I_D = 2.7$ A, $T_J = 125$ °C $V_{GS} = 2.5$ V, $I_D = 2.2$ A		0.060 0.095 0.085	0.080 0.128 0.120	Ω	
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	6			Α	
<b>g</b> <sub>FS</sub>	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 2.7 \text{ A}$		8		S	
Dvnamio	Characteristics						
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$		310		pF	
Coss	Output Capacitance	f = 1.0 MHz		80		pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			40		pF	
Switchin	g Characteristics (Note 2)						
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 10 \text{ V}, I_D = 1 \text{ A},$		5	15	ns	
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		8.5	17	ns	
t <sub>d(off)</sub>	Turn-Off Delay Time			11	20	ns	
t <sub>f</sub>	Turn-Off Fall Time			3	10	ns	
$\overline{Q_g}$	Total Gate Charge	$V_{DS} = 10 \text{ V}, I_D = 2.7 \text{ A},$		3.5	5	nC	
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 4.5 V		0.55		nC	
Q <sub>gd</sub>	Gate-Drain Charge			0.95		nC	
Drain-Sc	ource Diode Characteristics an	d Maximum Ratings					
	Maximum Continuous Drain-Source Did				0.8	Α	
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 0.8 A (Note 2)		0.77	1.2	V	

<sup>1.</sup> R<sub>eJA</sub> is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>BUC</sub> is guaranteed by design while R<sub>BCA</sub> is determined by the user's board design. Both devices are assumed to be operating and sharing the dissipated heat energy equally.



a) 130 °C/W when mounted on a 0.125 in² pad of 2 oz. copper.



b) 140 °C/W when mounted on a 0.005 in² pad of 2 oz. copper.



c) 180 °C/W on a minimum mounting pad.

Scale 1: 1 on letter size paper

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

### **Typical Characteristics**

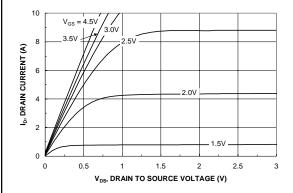


Figure 1. On-Region Characteristics.

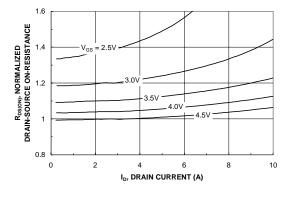


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

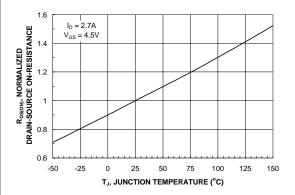


Figure 3. On-Resistance Variation with Temperature.

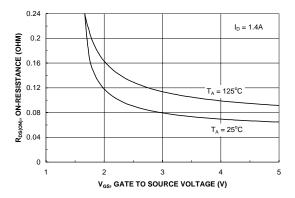


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

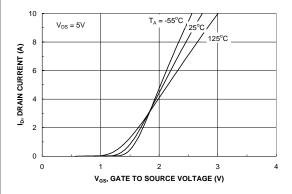


Figure 5. Transfer Characteristics.

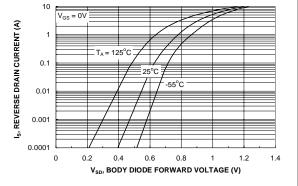
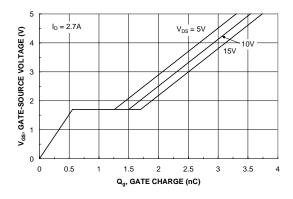


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

### Typical Characteristics (continued)



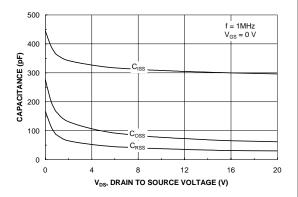
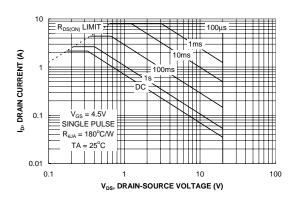


Figure 7. Gate-Charge Characteristics.





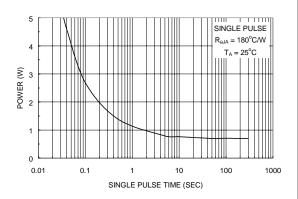


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

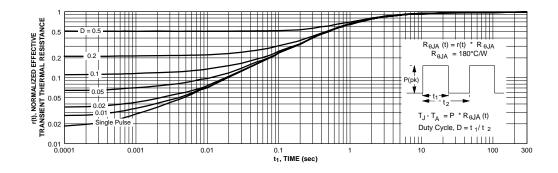
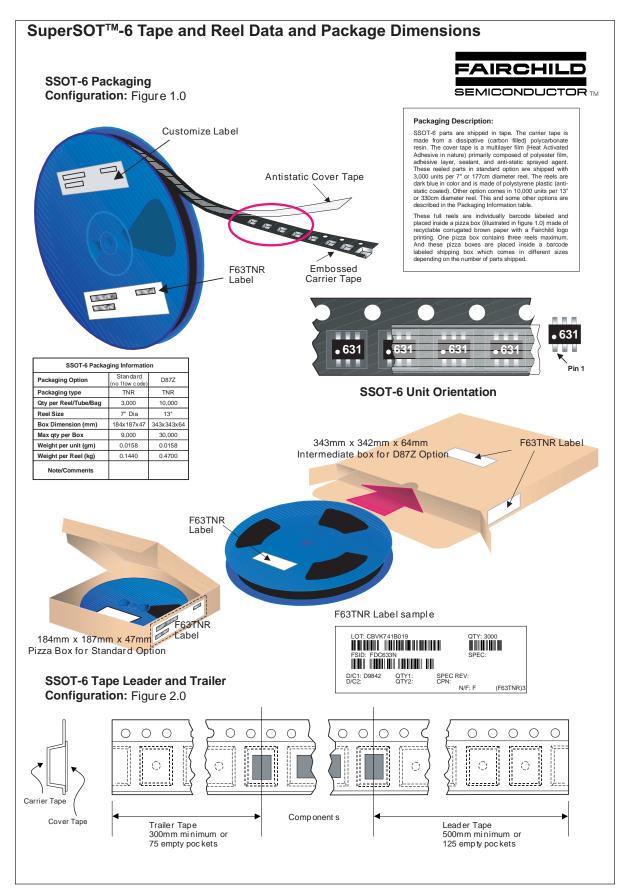


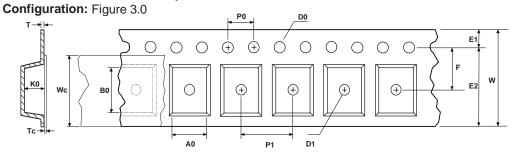
Figure 11. Transient Thermal Response Curve.

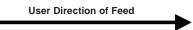
Thermal characterization performed using the conditions described in Note 1c. Transient themal response will change depending on the circuit board design.



### SuperSOT<sup>™</sup>-6 Tape and Reel Data and Package Dimensions, continued

### **SSOT-6 Embossed Carrier Tape**



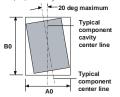


	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-6 (8mm)	3.23 +/-0.10	3.18 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.255 +/-0.150	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



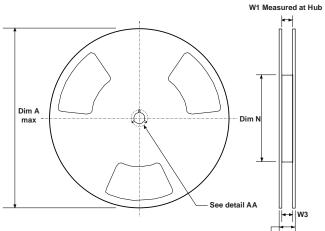
Sketch B (Top View)
Component Rotation



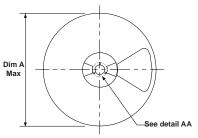
Sketch C (Top View)

Component lateral movement

# SSOT-6 Reel Configuration: Figure 4.0





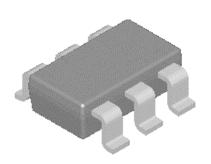


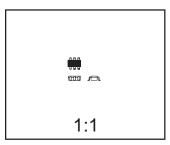
## 7" Diameter Option B Min Dim D DETAIL AA

	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

### SuperSOT<sup>™</sup>-6 Tape and Reel Data and Package Dimensions, continued

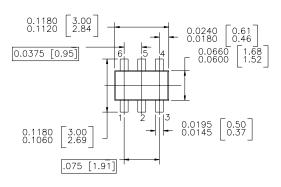
## SuperSOT -6 (FS PKG Code 31, 33)

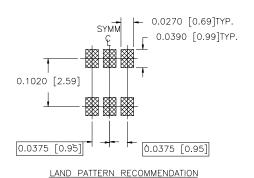




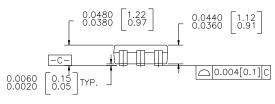
Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

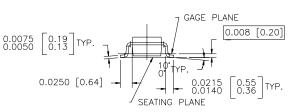
Part Weight per unit (gram): 0.0158





CONTROLLING DIMENSION IS INCH VALUES IN [ ] ARE MILLIMETERS





NOTES: UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH: 150 MICROINCHES 93.81 MICROMETERS) MINIMUM TIN / LEAD (SOLDER) ON COPPER.

2.0 NO JEDEC REGISTRATION AS OF JULY 1996

SUPER SOT 6 LEADS



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